

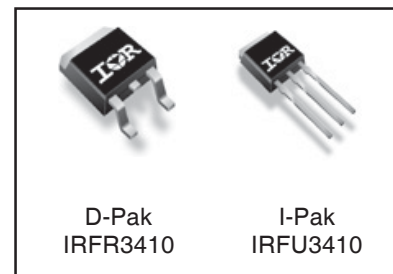
Applications

- High frequency DC-DC converters

V_{DS}	$R_{DS(on)}$ max	I_D
100V	39m Ω	31A ^⑥

Benefits

- Low Gate-to-Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective C_{OSS} to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current



Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V _{DS}	Drain-Source Voltage	100	V
V _{GS}	Gate-to-Source Voltage	± 20	
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	31⑥	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	22	
I _{DM}	Pulsed Drain Current①	125	
P _D @T _C = 25°C	Maximum Power Dissipation	110	W
P _D @T _A = 25°C	Maximum Power Dissipation	3.0	
	Linear Derating Factor	0.71	W°C
dv/dt	Peak Diode Recovery dv/dt ③	15	V/ns
T _J	Operating Junction and	-55 to + 175	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.4	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)*	—	40	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

Notes ① through ⑥ are on page 10

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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	—	—	V	$V_{GS} = 0V$, $I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.11	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1\text{mA}$ ④
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	34	39	m Ω	$V_{GS} = 10V$, $I_D = 18A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 100V$, $V_{GS} = 0V$
		—	—	250		$V_{DS} = 80V$, $V_{GS} = 0V$, $T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -20V$

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	33	—	—	S	$V_{DS} = 25V$, $I_D = 18A$
Q_g	Total Gate Charge	—	37	56	nC	$I_D = 18A$ $V_{DS} = 50V$ $V_{GS} = 10V$, ④
Q_{gs}	Gate-to-Source Charge	—	10	—		
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	11	—		
$t_{d(on)}$	Turn-On Delay Time	—	12	—	ns	$V_{DD} = 50V$ $I_D = 18A$ $R_G = 9.1\Omega$ $V_{GS} = 10V$ ④
t_r	Rise Time	—	27	—		
$t_{d(off)}$	Turn-Off Delay Time	—	40	—		
t_f	Fall Time	—	13	—		
C_{iss}	Input Capacitance	—	1690	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	220	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	26	—		$f = 1.0\text{MHz}$
C_{oss}	Output Capacitance	—	1640	—		$V_{GS} = 0V$, $V_{DS} = 1.0V$, $f = 1.0\text{MHz}$
C_{oss}	Output Capacitance	—	130	—		$V_{GS} = 0V$, $V_{DS} = 80V$, $f = 1.0\text{MHz}$
$C_{oss \text{ eff.}}$	Effective Output Capacitance	—	250	—		$V_{GS} = 0V$, $V_{DS} = 0V$ to $80V$ ⑤

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	140	mJ
I_{AR}	Avalanche Current①	—	18	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	31⑥	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	125		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}$, $I_S = 18A$, $V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	84	—	ns	$T_J = 25^\circ\text{C}$, $I_F = 18A$
Q_{rr}	Reverse Recovery Charge	—	260	—	nC	$di/dt = 100A/\mu s$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

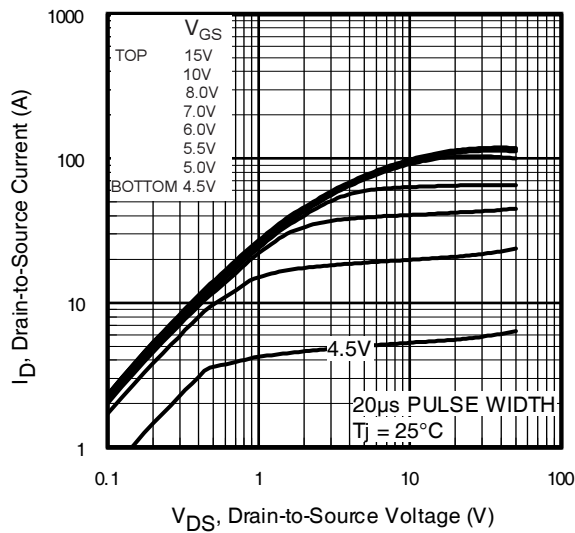


Fig 1. Typical Output Characteristics

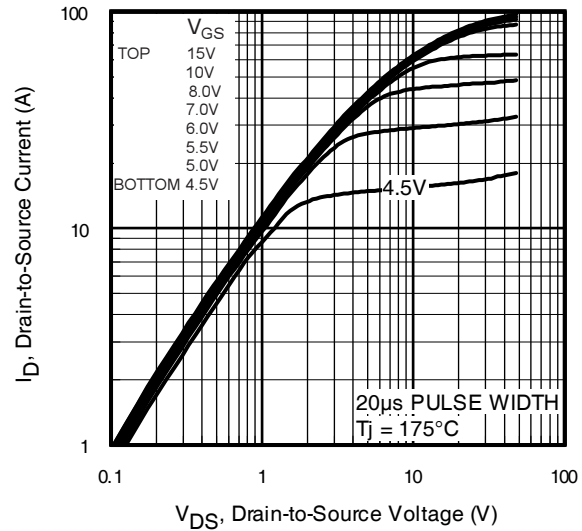


Fig 2. Typical Output Characteristics

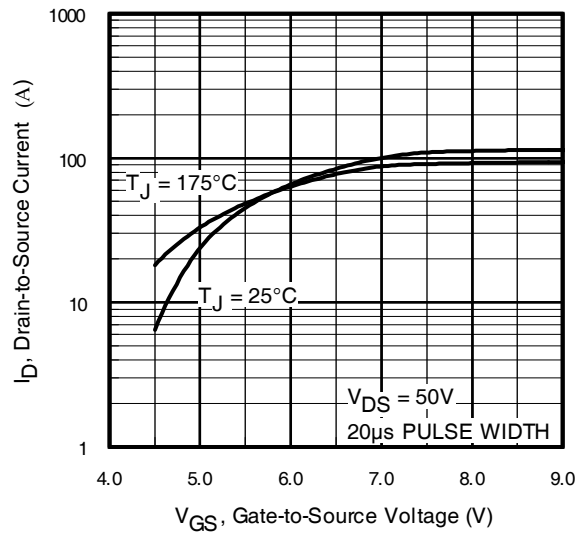


Fig 3. Typical Transfer Characteristics

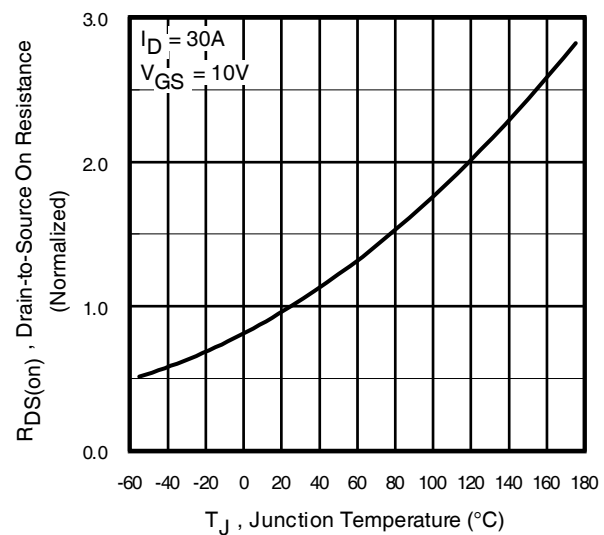


Fig 4. Normalized On-Resistance Vs. Temperature

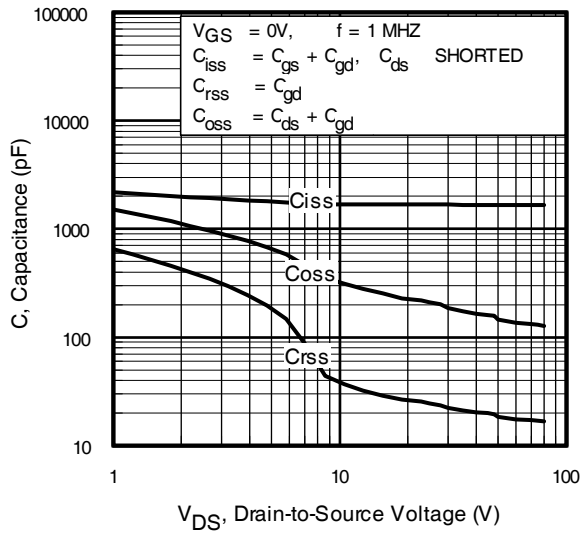


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

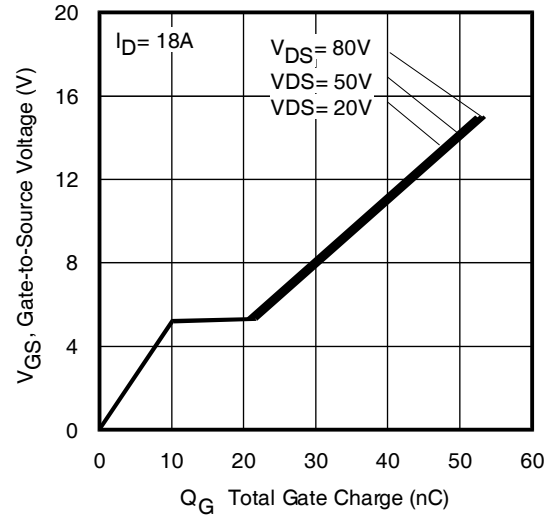


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

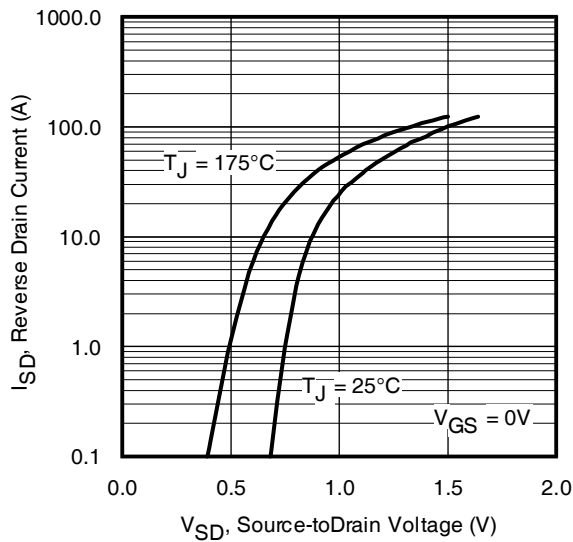


Fig 7. Typical Source-Drain Diode Forward Voltage

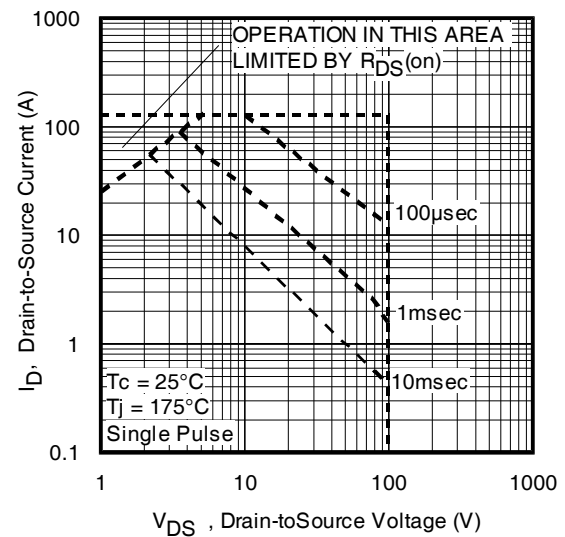


Fig 8. Maximum Safe Operating Area

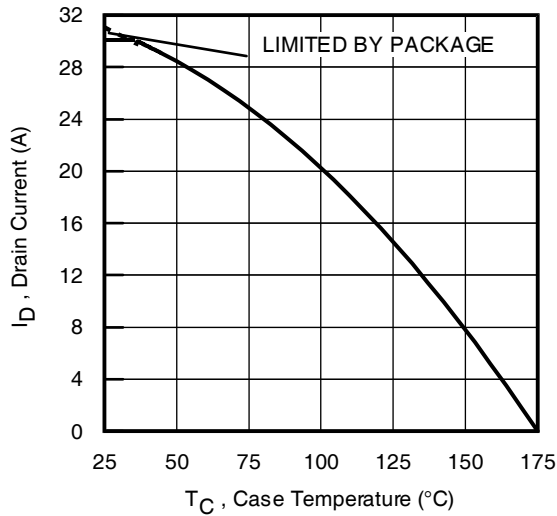


Fig 9. Maximum Drain Current Vs. Case Temperature

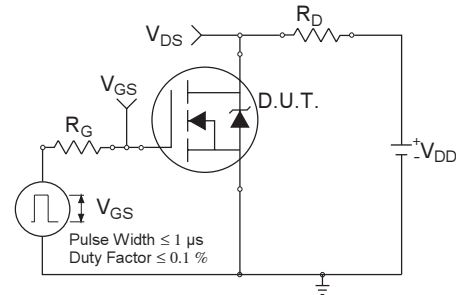


Fig 10a. Switching Time Test Circuit

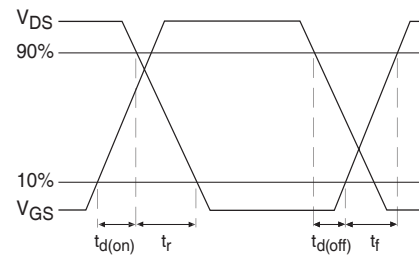


Fig 10b. Switching Time Waveforms

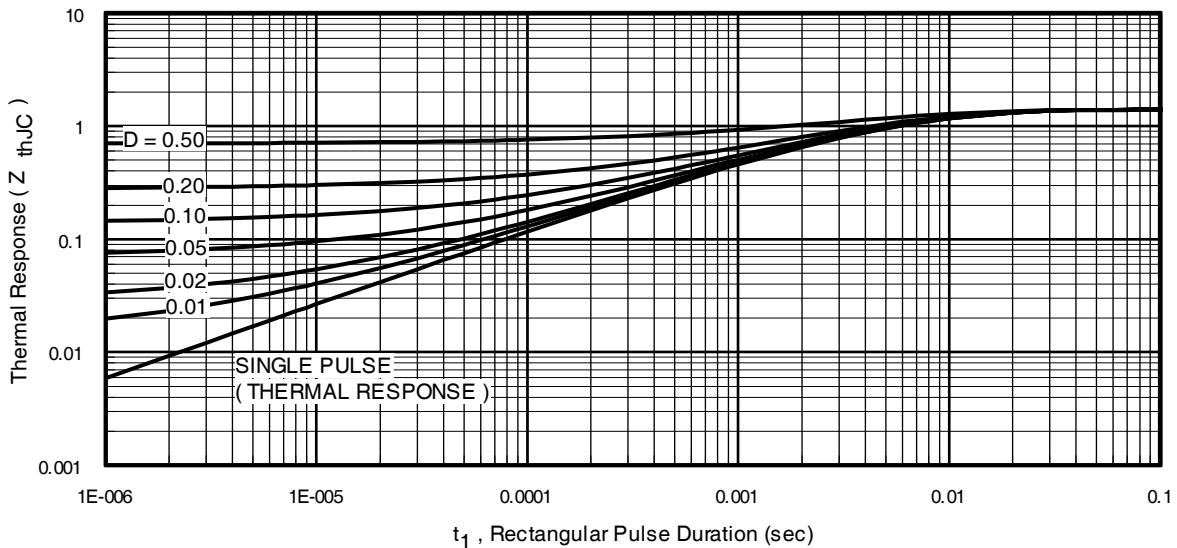


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

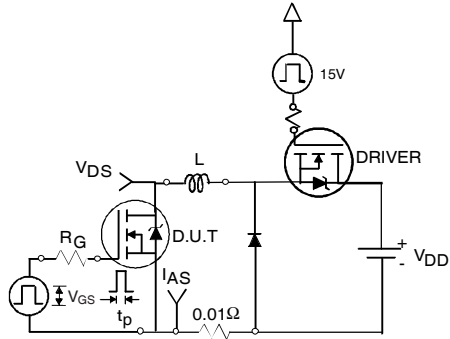


Fig 12a. Unclamped Inductive Test Circuit

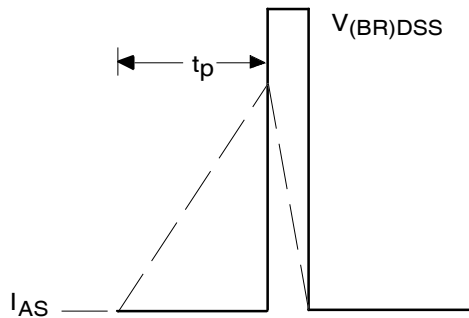


Fig 12b. Unclamped Inductive Waveforms

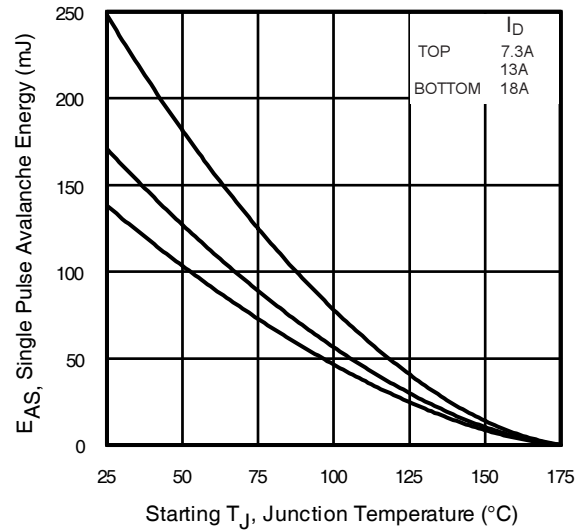


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

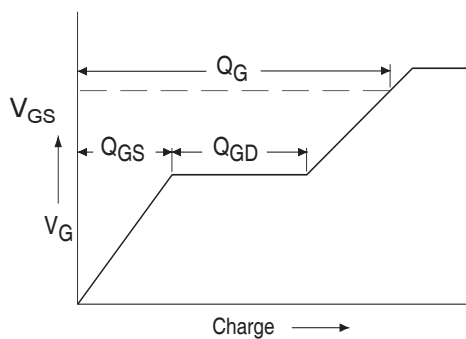


Fig 13a. Basic Gate Charge Waveform

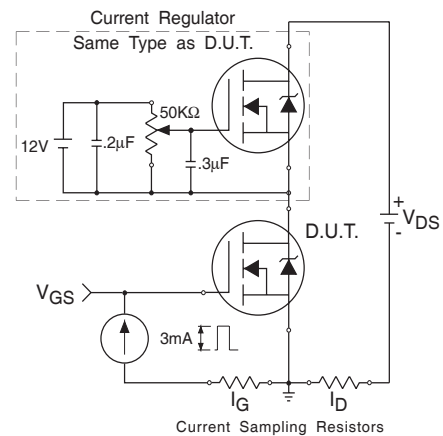
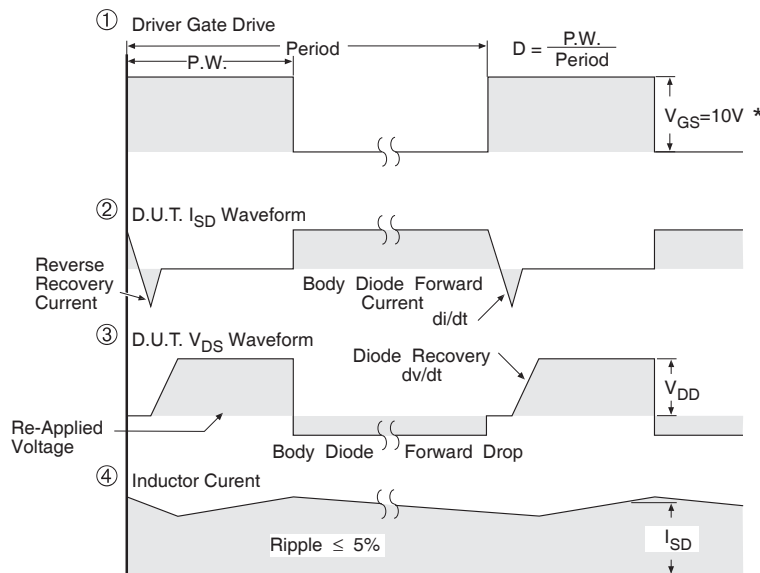
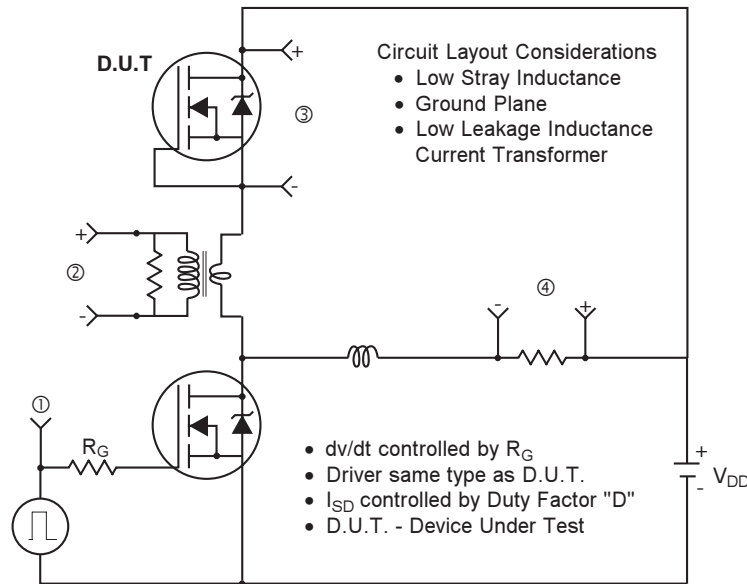


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-Channel HEXFET® Power MOSFETs

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Technical drawing of a mechanical part showing dimensions and feature control frames. The drawing includes a main view and a detail view (DETAIL A).

Dimensions:

- Overall width: E
- Distance from left face to center of hole 1: $b.5$
- Distance from left face to center of hole 2: 1.5
- Distance from left face to center of hole 3: $2 \times b.2$
- Distance from center of hole 3 to right face: $2 \times L.5$
- Distance from center of hole 3 to center of hole 4: $3 \times b$
- Distance from center of hole 4 to right face: $L.4$
- Overall height: H
- Distance from top face to center of hole 1: $c.2$
- Distance from top face to center of hole 2: $a.1$

Feature Control Frames:

- Feature 1 (Hole): $\text{Ø}0.010 \text{ (0.25) } \text{C} \text{A} \text{B}$
- Feature 2 (Hole): $\text{Ø}0.010 \text{ (0.25) } \text{C} \text{A} \text{B}$
- Feature 3 (Hole): $\text{Ø}0.010 \text{ (0.25) } \text{C} \text{A} \text{B}$
- Feature 4 (Hole): $\text{Ø}0.010 \text{ (0.25) } \text{C} \text{A} \text{B}$

Detail View (DETAIL A): Shows a cross-section of the part with dimensions $a.1$ and $c.2$, and a section line $A-A$.

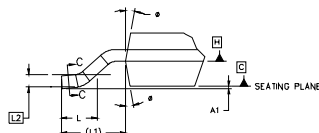


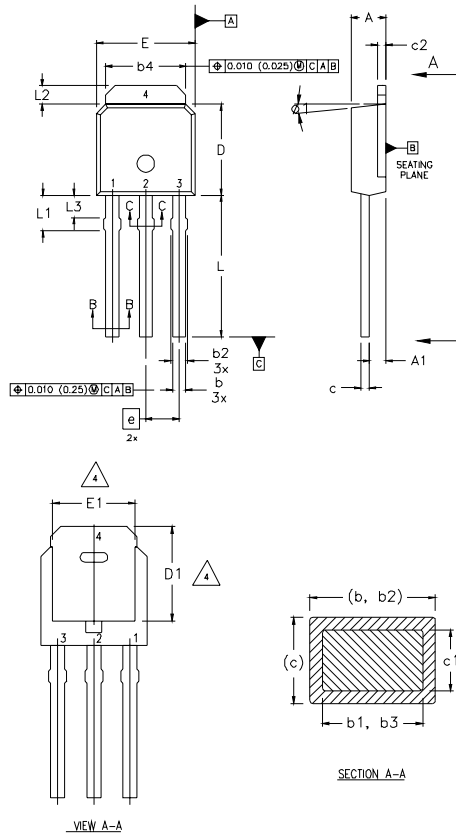
Diagram illustrating the geometry of a rectangular plate with a central hole, showing dimensions and plating. The outer dimensions are b (width) and c (height). The inner dimensions of the hole are b_1 (width) and c_1 (height). The plating metal is indicated by hatching on the outer surface. The diagram is labeled "SECTION C-C".

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.088	.094	
A1		.005		.005	
b	0.64	0.89	.025	.035	5
b1	0.64	0.79	.025	0.031	5
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	
c	0.46	0.61	.018	.024	5
c1	0.41	0.56	.016	.022	5
c2	.046	0.80	.018	.035	5
D	5.97	6.22	.235	.245	6
D1	5.71	-	.205	-	4
E	6.85	6.73	.260	.265	6
E1	4.32	-	.170	-	4
e	.009 BSC				
H	8.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	.100 REF.				
L2	.009 BSC				
L3	0.89	1.27	.035	.050	
L4	1.01	1.02	.040	.040	
L5	1.14	1.52	.045	.060	5
#	0°	10°	0°	10°	
#1	0°	15°	0°	15°	

Diagram illustrating the markings on a MOSFET package:

- INTERNATIONAL RECTIFIER LOGO**: Points to the IR logo on the package.
- PART NUMBER**: Points to the text **IRFR120** on the package.
- DATE CODE**: Points to the text **P=** on the package.
- PRODUCT (OPTIONAL)**: Points to the text **12 34** on the package.
- YEAR 9 = 1999**: Points to the text **12** on the package.
- WEEK 16**: Points to the text **34** on the package.
- A = ASSEMBLY SITE CODE**: Points to the text **12** on the package.
- ASSEMBLY LOT CODE**: Points to the text **12** on the package.

I-Pak (TO-251AA) Package Outline



NOTES:

- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 4 THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
- 5 LEAD DIMENSION UNCONTROLLED IN L3.
- 6 DIMENSION b1, b3 APPLY TO BASE METAL ONLY.
- 7 OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.
- 8 CONTROLLING DIMENSION : INCHES.

LEAD ASSIGNMENTS

HEXFET

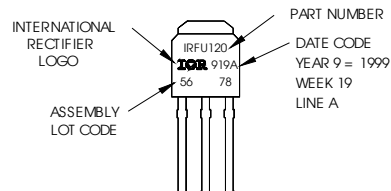
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	0.086	.094	
A1	0.89	1.14	0.035	0.045	
b	0.64	0.89	0.025	0.035	
b1	0.64	0.79	0.025	0.031	4
b2	0.76	1.14	0.030	0.045	
b3	0.76	1.04	0.030	0.041	
b4	5.00	5.46	0.195	0.215	4
c	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	
c2	.046	0.86	0.018	0.035	
D	5.97	6.22	0.235	0.245	3, 4
D1	5.21	—	0.205	—	4
E	6.35	6.73	0.250	0.265	3, 4
E1	4.32	—	0.170	—	4
e	2.29		0.090 BSC		
L	8.89	9.60	0.350	0.380	
L1	1.91	2.29	0.075	0.090	
L2	0.89	1.27	0.035	0.050	4
L3	1.14	1.52	0.045	0.060	5
ø1	0"	15'	0"	15'	

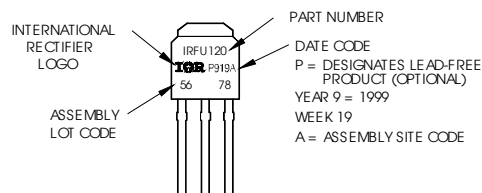
I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120
WITH ASSEMBLY
LOT CODE 5678
ASSEMBLED ON WW 19, 1999
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position indicates "Lead-Free"



OR

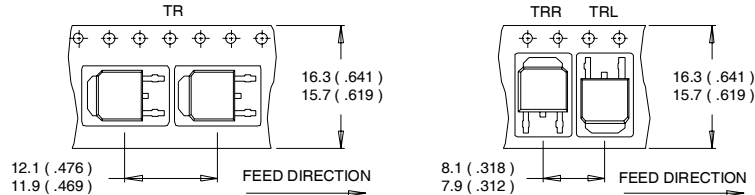


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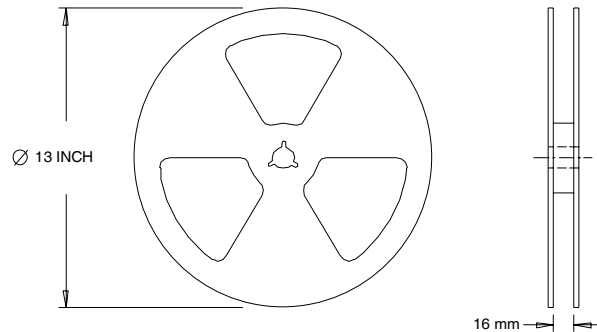
International
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D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. OUTLINE CONFORMS TO EIA-481.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
 - ② Starting $T_J = 25^\circ\text{C}$, $L = 0.85\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 18\text{A}$.
 - ③ $I_{SD} \leq 18\text{A}$, $di/dt \leq 360\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$
 - ④ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.
 - ⑤ C_{OSS} eff. is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 80% V_{DSS}
 - ⑥ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 30A.
- * When mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

International
IR Rectifier

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TAC Fax: (310) 252-7903

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